

METHOD OF MANUFACTURING A SEMI-CONDUCTOR DEVICE

Abstract

There are provided the steps of forming a first conductive layer, an oxide dielectric layer, and a second conductive layer sequentially over a first insulating layer formed over a semiconductor substrate, forming a capacitor consisting of an upper electrode, a dielectric layer, and a lower electrode made by patterning the second conductive layer, the oxide dielectric layer, and the first conductive layer, forming a second insulating layer over the capacitor and the first insulating layer, forming a hole in the second insulating layer on the upper electrode, and supplying an activated oxygen to the capacitor via the hole in a state that the semiconductor substrate is heated.